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April 1st, 2010 Renesas Electronics Corporation

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MOS FIELD EFFECT TRANSISTOR μ PA1951

P-CHANNEL MOS FIELD EFFECT TRANSISTOR FOR SWITCHING

DESCRIPTION

The μ PA1951 is a switching device, which can be driven directly by a 1.8 V power source.

The device features a low on-state resistance and excellent switching characteristics, and is suitable for applications such as power switch of portable machine and so on.

FEATURES

- 1.8 V drive available
- Low on-state resistance

RDS(on)1 = 88 m Ω MAX. (Vgs = -4.5V, ID = -1.5 A)

 $R_{DS(on)2} = 114 \text{ m}\Omega \text{ MAX.} \text{ (Vgs} = -3.0 \text{ V, Ip} = -1.5 \text{ A)}$

RDS(on)3 = 133 m Ω MAX. (VGS = -2.5 V, ID = -1.5 A)

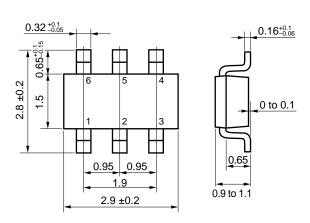
 $R_{DS(on)4} = 234 \text{ m}\Omega \text{ MAX.} \text{ (Vgs} = -1.8 \text{ V, Ip} = -1.0 \text{ A)}$

ORDERING INFORMATION

PART NUMBER	PACKAGE
μ PA1951TE	SC-95 (Mini Mold Thin Type)

Marking: TN

PACKAGE DRAWING (Unit: mm)

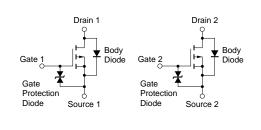


- 6: Drain 1 1: Gate 1
- 4: Drain 2
- 5: Source 1
- 3: Gate 2 2: Source 2

ABSOLUTE MAXIMUM RATINGS (TA = 25°C)

Drain to Source Voltage (Vgs = 0 V)	VDSS	-12	V
Gate to Source Voltage (Vps = 0 V)	Vgss	∓8.0	V
Drain Current (DC)	I _{D(DC)}	∓2.5	Α
Drain Current (pulse) Note1	I _{D(pulse)}	∓10	Α
Total Power Dissipation (2 units) Note2	P _{T1}	1.15	W
Total Power Dissipation (1 unit) Note2	P _{T2}	0.57	W
Channel Temperature	Tch	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

EQUIVALENT CIRCUITS



Notes 1. PW \leq 10 μ s, Duty Cycle \leq 1%

2. Mounted on FR-4 board of 5000 mm² x 1.1 mm, $t \le 5$ sec.

Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

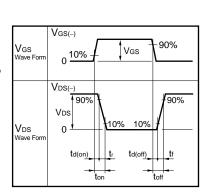
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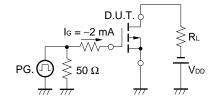
ELECTRICAL CHARACTERISTICS (TA = 25°C)

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	Ipss	V _{DS} = -12 V, V _{GS} = 0 V			-10	μΑ
Gate Leakage Current	lgss	$V_{GS} = \mp 8.0 \text{ V}, V_{DS} = 0 \text{ V}$			∓10	μΑ
Gate Cut-off Voltage	V _{GS(off)}	$V_{DS} = -10 \text{ V}, I_{D} = -1.0 \text{ mA}$	-0.45	-0.75	-1.5	V
Forward Transfer Admittance	y fs	$V_{DS} = -10 \text{ V}, I_{D} = -1.5 \text{ A}$	1.0	4.7		S
Drain to Source On-state Resistance	RDS(on)1	V _G S = −4.5 V, I _D = −1.5 A		70	88	mΩ
	RDS(on)2	V _G S = −3.0 V, I _D = −1.5 A		85	114	mΩ
	RDS(on)3	V _G S = −2.5 V, I _D = −1.5 A		100	133	mΩ
	RDS(on)4	Vgs = -1.8 V, ID = -1.0 A		140	234	mΩ
Input Capacitance	Ciss	V _{DS} = -10 V		270		pF
Output Capacitance	Coss	V _G S = 0 V		90		pF
Reverse Transfer Capacitance	Crss	f = 1.0 MHz		45		pF
Turn-on Delay Time	td(on)	$V_{DD} = -6.0 \text{ V}, \text{ ID} = -1.5 \text{ A}$		14		ns
Rise Time	tr	Vgs = -4.0 V		90		ns
Turn-off Delay Time	td(off)	$R_G = 10 \Omega$		150		ns
Fall Time	tf			130		ns
Total Gate Charge	Q _G	V _{DD} = -10 V		2.4		nC
Gate to Source Charge	Qgs	V _G S = -4.0 V		0.6		nC
Gate to Drain Charge	Q _{GD}	I _D = -2.5 A		0.8		nC
Body Diode Forward Voltage	V _{F(S-D)}	IF = 2.5 A, VGS = 0 V		0.87		V

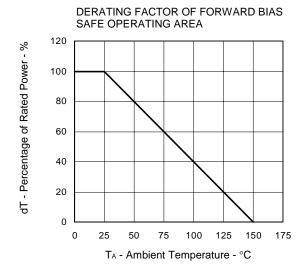
TEST CIRCUIT 1 SWITCHING TIME

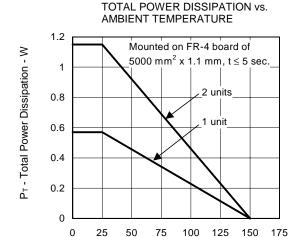


TEST CIRCUIT 2 GATE CHARGE



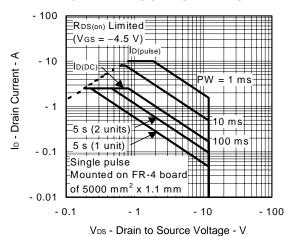
TYPICAL CHARACTERISTICS (TA = 25°C)



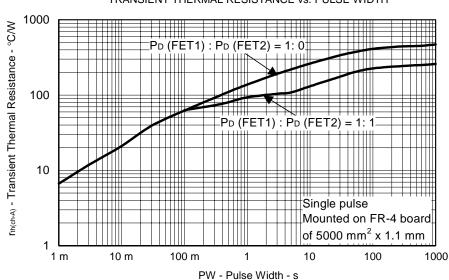


T_A - Ambient Temperature - °C

FORWARD BIAS SAFE OPERATING AREA

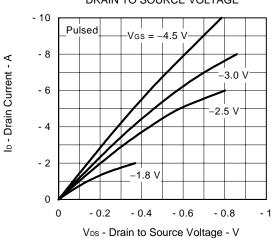


TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH

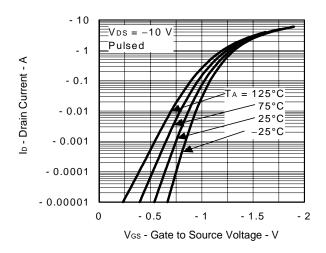


3

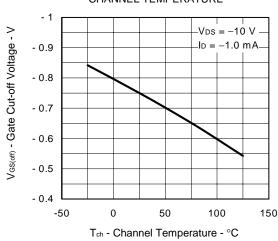
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



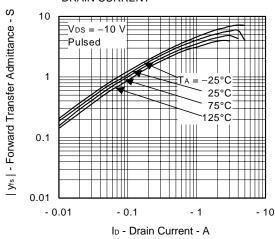
FORWARD TRANSFER CHARACTERISTICS



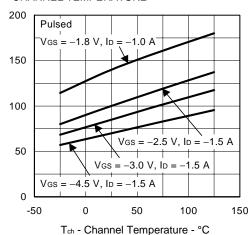
GATE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE



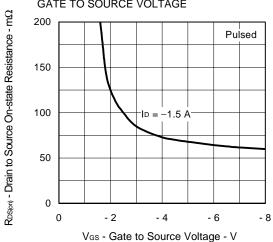
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



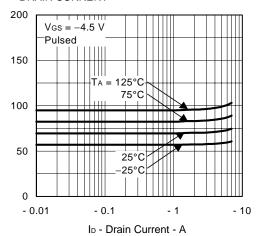
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



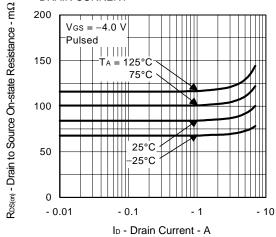
RDS(on) - Drain to Source On-state Resistance - mΩ

RDS(m) - Drain to Source On-state Resistance - mΩ

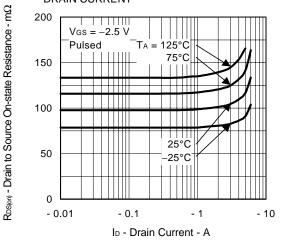
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



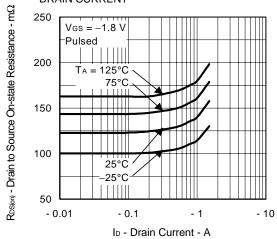
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



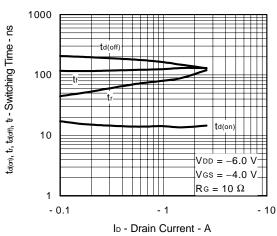
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



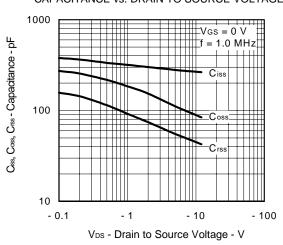
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



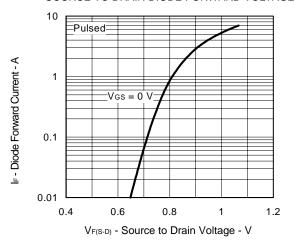
SWITCHING CHARACTERISTICS



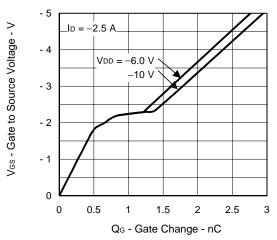
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



SOURCE TO DRAIN DIODE FORWARD VOLTAGE



DYNAMIC INPUT/OUTPUT CHARACTERISTICS



NEC μ PA1951

[MEMO]

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